

UNIVERSITATEA POLITEHNICA DIN BUCUREȘTI

FIȘA DE VERIFICARE A ÎNDEPLINIRII STANDARDELOR DE ABILITARE [PROFESOR]

CANDIDAT: Conf. Dr. Ing. DRĂGHICI Florin

Departamentul Dispozitive, Circuite și Arhitecturi Electronice (DCAE), Facultatea de Electronică, Telecomunicații și Tehnologia Informației (ETTI) - UPB

Condiții	Îndeplinire condiții	
A. Doctor	Diploma de Doctor în domeniul Inginerie Electronică și Telecomunicații, Seria D, Nr. 0002517 din 20.09.2004 emisă de Universitatea Politehnica din București	
B. Îndeplinirea standardelor minime naționale conform OMECTS nr. 6129/20.12.2016; MO, I, 123/15.02.2017 [Comisia CNATDCU nr. 11]	Standarde îndeplinite, conform Comisiei CNATDCU Nr.11, Inginerie Electronică și Telecomunicații, Anexată: Fișa de calcul și de susținere a îndeplinirii standardelor minime specifice domeniului, în acord cu realizările menționate	
Condiții minimale [Punctaj]	Minim prevăzut	Realizat
A1. Activitatea didactică și profesională	100	121,6
A2. Activitatea de cercetare	600	664
A3. Recunoașterea și impactul activității	150	300,3
TOTAL (A)	850	1085,9
Condiții minimale obligatorii pe subcategorii [Număr]	Minim prevăzut	Realizat
A1.1.1 - A1.1.2. Cărți și capitole în cărți de specialitate	1	2
A2.1. Articole în reviste cotate ISI și în volumele unor manifestări științifice ISI (WOS)	15 / minim 3 în reviste cotate Q1 sau Q2	55/7
A2.4.1. Granturi/proiecte câștigate prin competiție (Director/responsabil)	2	2
A3.1.1 - A3.1.2 Număr de citări în cărți, reviste și volume ale unor manifestări științifice ISI (WOS)	25	113
Factor de impact cumulată pentru publicații	10	36,517
C. Atestarea studiilor (diploma + Foi Matricole) și a altor realizări profesionale	Diploma de Licență , în profilul Electronic, specializarea Microelectronică, Seria R, Nr. 0004516 din 02.11.1998 emisă de Universitatea Politehnica din București, Facultatea de Electronică, Telecomunicații și Tehnologia Informației Diploma de Studii aprofundate , în profilul Electronic, specializarea Microsisteme, Seria D, Nr. 0002598 din 26.11.1999 emisă de Universitatea Politehnica din București, Facultatea de Electronică, Telecomunicații și Tehnologia Informației Certificat de absolvire a studiilor psihopedagogice , Seria B, Nr. 0003726 din 07.06.2001 eliberat de Departamentul pentru pregătirea personalului didactic al Universității Politehnica din București Alte acte de atestare a studiilor/realizărilor profesionale.....	

Subsemnatul DRĂGHICI D. Florin, din Departamentul Dispozitive, Circuite și Arhitecturi Electronice, Facultatea de Electronică, Telecomunicații și Tehnologia Informației, din Domeniul de studii univ. Inginerie Electronică, Telecomunicații și Tehnologii Informaționale, arondat Comisiei de specialitate CNATDCU [OMECTS 4106/2016] Nr. 11, Inginerie Electronică și Telecomunicații, declar pe propria răspundere, cunoscând prevederile art. 292 privind falsul în declarații, din Legea 286/2009 - Codul Penal, că sunt îndeplinite toate Standardele minime prevăzute de Metodologia UPB 2017 pentru susținerea tezei de abilitare și OMECTS 6129/2016 [C + P], în momentul înscrierii la concurs, și susțin veridicitatea informațiilor prezentate în dosar și în materialul de mai sus. Lucrările considerate a fi incluse în Baza ISI Thomson Reuters sau în alte Baze de Date Internaționale [BDI] sunt vizibile în aceste baze, în dreptul numelui candidatului, la aceasta dată.

Candidat,
DRĂGHICI D. Florin

Data,
13.10.2021

ÎN CONTINUARE: Fișa de calcul și de susținere a îndeplinirii standardelor minime specifice domeniului, în acord cu realizările menționate

PREZENTARE DETALIATĂ

Nr.crt.	A1 - Activitate didactică și profesională	Tip [1]	Nr. Autori	>50 biblioteci străine conform WorldCat [2]	Punctaj
	A1.1.1 Cărți de autor sau capitole [1] de specialitate în edituri cu ISBN (Cărți / monografii) - internaționale				0.000
	A1.1.2 Cărți de autor sau capitole de specialitate în edituri cu ISBN (Cărți / monografii) - naționale	Tip [1]	Nr. Autori		
1	F. Drăghici, "Amplificatoare. Noțiuni de proiectare", Editura Matrix Rom, București, 2021, ISBN 978-606-25-0665-0, 111 pagini.	Carte	1		50.000
2	G. Brezeanu, F. Drăghici, "Circuite Electronice Fundamentale", Editura Niculescu, București, 2013, ISBN 978-973-748-745-2, 314 pagini.	Carte	2		25.000
	A1.2.1 Material didactic / Lucrări didactice publicate în edituri cu ISBN (Manuale didactice)	Tip [1]	Nr. Autori		
1	F. Drăghici, I. Rusu, L. Teodorescu, "Circuite Electronice - Îndrumar de Laborator", Editura Hamașniș, București, 2016, ISBN 978-606-27-0397-4, 86 pagini.	Carte	3		13.333
2	I. Rusu, F. Babarada, F. Drăghici, "Dispozitive Electronice - Îndrumar de Laborator", Editura Rosetti Educațional, București, 2011, ISBN 978-973-7881-71-7, 108 pagini.	Carte	3		13.333
3	G. Brezeanu, F. Drăghici, F. Mitu, G. Dilimoț, "Circuite electronice fundamentale - probleme", Editura Rosetti Internațional, București, ediția III-2014, ISBN 978-973-8270-24-4, 169 pagini, ediție revizuită	Carte	4		10.000
	G. Brezeanu, F. Drăghici, F. Mitu, G. Dilimoț, "Circuite electronice fundamentale - probleme", Editura Rosetti Educațional, București, ediția II-2008, ISBN 978-973-7881-39-7, 168 pagini.				
	G. Brezeanu, F. Drăghici, F. Mitu, G. Dilimoț, "Circuite electronice fundamentale - probleme", Editura ALL BECK, București, ediția I - 2005, ISBN 973-655-758-8, 168 pagini.				
4	G. Brezeanu, F. Drăghici, F. Mitu, G. Dilimoț, "Dispozitive electronice - probleme", Editura Rosetti Educațional, București, 2009, ISBN 978-973-7881-57-1, 207 pagini, ediție revizuită	Carte	4		10.000
	G. Brezeanu, G. Dilimoț, F. Mitu, F. Drăghici, "Probleme de Dispozitive și Circuite Electronice", Editura IT GRUP, București, ediția III- 2006, ISBN 973-85715-2-9, 207 pagini.				
	G. Brezeanu, G. Dilimoț, F. Mitu, F. Drăghici, "Probleme de Dispozitive și Circuite Electronice", Editura IT GRUP, București, ediția II - 2004, ISBN 973-85715-2-9, 207 pagini.				
	G. Brezeanu, G. Dilimoț, F. Mitu, F. Drăghici, "Probleme de Dispozitive și Circuite Electronice", Editura IT GRUP, București, ediția I - 2001, ISBN 973-99959-6-9, 207 pagini.				
	Total A1				121.667

Nr.crt.	A2 - Activitatea de cercetare	Baza de date [4]	Nr. Autori	Factor impact [3] (conf. Top [10])	Punctaj
	A2.1 Articole în reviste cotate ISI, și lucrări în volumele unor manifestări științifice indexate ISI				
1	G-C. Ilie (Chiranu), C. Tudoran, O. Neagoie, F. Drăghici, G. Brezeanu, "Nonvolatile Analog Switch for Low-Voltage Applications", Electronics 2021, pp. 1-10, (6), 736, https://doi.org/10.3390/electronics10060736 , WOS:000634338200001, Q2 în Domeniul ENGINEERING, ELECTRICAL & ELECTRONIC, IF=2,412 la data publicării articolului.	ISI-Q2	5	2.412	19.472
2	R. Pascu, G. Pristavu, G. Brezeanu, F. Drăghici, P. Godignon, C. Romanitan, M. Serbanescu, A. Tulbure, "60-700 K CTAT and PTAT Temperature Sensors with 4H-SiC Schottky Diodes", Sensors 2021, 21(3), 942, pp. 1-15, publicare online, https://doi.org/10.3390/s21030942 , eISSN: 1424-8220, WOS:000615521900001, Q1 în Domeniul INSTRUMENTS & INSTRUMENTATION, IF=3,576 la data depunerii tezei.	ISI-Q1	8	3.576	16.535
3	M. Boncu, C. Botezatu, F. Drăghici, "An algorithm-based method for accurate compensation of bandgap references over temperature", ROMANIAN JOURNAL OF INFORMATION SCIENCE AND TECHNOLOGY, Volume 24, Number 2, 2021, pp. 143-160, https://www.romjst.ro/full-texts/paper685.pdf , WOS:000668010700002, Q4 în Domeniul INSTRUMENTS & INSTRUMENTATION, IF=0,643 la data depunerii tezei.	ISI	3	0.643	14.763
4	M. Gheorghe, P. Mugar Svasta, S. Gheorghe, C. Ionescu, F. Drăghici, "Organic Electrical Passive Components Based on Polyaniline", 2020 IEEE 8th Electronics System-Integration Technology Conference (ESTC), 15-18 Sept. 2020, Tønsberg, Vestfold, Norway, Electronic ISBN:978-1-7281-6293-5, Print on Demand (PoD) ISBN:978-1-7281-6294-2, DOI: 10.1109/ESTC48849.2020.9229672 , pp. 1-4, WOS: 000631824100013	ISI	5	0.250	6.500
5	M. Boncu, C. Botezatu, F. Drăghici, "A precise method for compensating bandgap references over temperature", 2020 International Semiconductor Conference (CAS), 7-9 Oct. 2020, Sinaia, Romania, pp. 245-248, Electronic ISBN:978-1-7281-1073-8, Print on Demand (PoD) ISBN:978-1-7281-1074-5, DOI: 10.1109/CAS50358.2020.9268045 , WOS:000637264600055	ISI	3	0.250	10.833
6	G. Brezeanu, G. Pristavu, F. Drăghici, R. Pascu, F. Della Corte, S. Rascuna, "Enhanced Non-Uniformity Modeling of 4H-SiC Schottky Diode Characteristics Over Wide High Temperature and Forward Bias Ranges", IEEE JOURNAL OF THE ELECTRONIC DEVICES SOCIETY, Volume: 8, Pages: 1339-1344, 2020, DOI: 10.1109/JEDS.2020.3032799 , ISSN: 2168-6734, WOS:000589593200001, Q2 în Domeniul ENGINEERING, ELECTRICAL & ELECTRONIC, IF=2,555 la data publicării articolului.	ISI-Q2	6	2.555	16.942
7	F. Drăghici, G. Brezeanu, G. Pristavu, R. Pascu, M. Badila, A. Pribeanu, E. Ceuca, "400°C Sensor Based on Ni/4H-SiC Schottky Diode for Reliable Temperature Monitoring in Industrial Environments". Sensors 2019, 19, 2384, publicare online https://doi.org/10.3390/s19102384 , pp. 1-16, WOS:000471014500171, Q1 în Domeniul INSTRUMENTS & INSTRUMENTATION, IF=3,576 la data depunerii tezei.	ISI-Q1	7	3.576	18.897
8	N. Pavel, R. Chiriac, A. Birtas, F. Drăghici, M. Dinca, "On the improvement by laser ignition of the performances of a passenger car gasoline engine", OPTICS EXPRESS, Vol. 27, No. 8, 2019, pp. A385-A396, https://doi.org/10.1364/OE.27.00A385 , WOS:000464614400013, Q1 în Domeniul OPTICS, IF=3,894 la data depunerii tezei.	ISI-Q1	5	3.894	28.364
9	G. Pristavu, G. Brezeanu, R. Pascu, F. Drăghici, M. Bădilă, "Characterization of non-uniform Ni/4H-SiC Schottky diodes for improved responsivity in high-temperature sensing", Materials Science in Semiconductor Processing, Vol. 94, 2019, Pages 64-69, ISSN 1369-8001, https://doi.org/10.1016/j.mssp.2019.01.018 , (http://www.sciencedirect.com/science/article/pii/S1369800118316986), WOS:000458507800009, Q1 în Domeniul ENGINEERING, ELECTRICAL & ELECTRONIC, IF=3,927 la data depunerii tezei.	ISI-Q1	5	3.927	28.562

10	A. Enache, F. Drăghici, G. Pristavu, G. Brezeanu, "Voltage Controlled Oscillator for Small-Signal Capacitance Sensing", in Proceedings of the 2019 International Semiconductor Conference (CAS), Sinaia, Romania, 9-11 Oct. 2019, pp: 323-326, DOI: 10.1109/SMICND.2019.8923728, INSPEC Accession Number: 19222668, WOS:000514295300068	ISI	4	0.250	8.125
11	A. Birtas, N. Boicea, G. Croitoru, M. Dinca, N. Pavel, F. Draghici, R. Chiriac, "On the possibility to improve petrol engine operation by laser ignition", Energy Procedia, Vol. 157, pp. 1022-1028, Elsevier, 2019, ISSN: 1876-6102, DOI:10.1016/j.egypro.2018.11.269, WOS:000470998600112	ISI	7	0.250	4.643
12	N. Pavel, R. Chiriac, A. Birtas, N. Boicea, F. Draghici, G. Croitoru, M. Dinca, "Lean-Mixture Operation of a Passenger Car Gasoline Engine Ignited by Passively Q-switched Nd: YAG/Cr4+: YAG Laser Spark Plugs", in 2019 Conference on Lasers and Electro-Optics Europe and European Quantum Electronics Conference, OSA Technical Digest (Optical Society of America, 2019), paper cm_p_13, ISBN:978-1-7281-0469-0, DOI 10.1109/CLEOE-EQEC.2019.8872741, WOS:000630002701062	ISI	7	0.250	4.643
13	R.V. Petrica, M.D. Dobre, P. Coll, F. Draghici, G. Brezeanu, "Comparison of Level Shifter Architectures: Application to I/O Cell", in Proc. of. the 2018 International Semiconductor Conference (CAS), Sinaia, Romania, pp. 209-212, 2018, IEEE., DOI: 10.1109/SMICND.2018.8539796, WOS:000514386700041	ISI	5	0.250	6.500
14	R. Pascu, M. Danila, P. Varasteanu, M. Kusko, G. Pristavu, G. Brezeanu, F. Draghici, "Improved Ti/Pt/Au-n-Type Si Contacts by Post-Metallization Annealing in Nitrogen Atmosphere", in Proc. of. the 2018 International Semiconductor Conference (CAS), Sinaia, Romania, pp. 307-310, 2018, IEEE, DOI:10.1109/SMICND.2018.8539839, WOS:000514386700064	ISI	7	0.250	4.643
15	G. Brezeanu, G. Pristavu, F. Draghici, M. Badila, R. Pascu, "Characterization technique for inhomogeneous 4H-SiC Schottky contacts: A practical model for high temperature behavior", Journal of Applied Physics, Vol. 122, Article number: 084501 (2017); https://doi.org/10.1063/1.4999296, ISSN: 0021-8979, eISSN: 1089-7550, FI=2.16, pp. 084501-1-084501-12, WOS:000409117200029, Q2 in Domeniul PHYSICS, APPLIED, IF=2.546 la data depunerii tezei.	ISI-Q2	5	2.546	20.276
16	A. Birtas, N. Boicea, F. Draghici, R. Chiriac, G. Croitoru, M. Dinca T. Dascalu, N. Pavel, "On the assessment of performance and emissions characteristics of a SI engine provided with a laser ignition system", in (CAR2017) Book Series: IOP Conference Series-Materials Science and Engineering, Volume: 252 Article Number: UNSP 012071, pp. 1-8, ISSN: 1757-8981, DOI: 10.1088/1757-899X/252/1/012071, 2017, Accession Number: WOS:000419817200071, FI=0,25	ISI	8	0.250	4.063
17	A. Enache, I. Rusu, B. Bucur, F. Drăghici, G. Pristavu, M. P. Bucur, F. Enache, G. Brezeanu, "Experimental Characterization of a High Accuracy Amperometric Sense and Control Circuit for Three-Electrode Biosensors", in Proc. of the 40th International Semiconductor Conference, 11-14 Oct. 2017, Sinaia, Romania, pp.179-182, , ISSN: 1545-827X, ISBN: 978-1-5090-3985-2, INSPEC Accession Number: 17353983, DOI: 10.1109/SMICND.2017.8101193, WOS:000425844500037, FI=0,25	ISI	8	0.250	4.063
18	G. Pristavu, G. Brezeanu, R. Pascu, F. Draghici, M. Badila, I. Rusu, "Study on thermal sensitivity of highly inhomogeneous Ni/4H-SiC Schottky diode over a wide temperature range", in Proc. of the 40th International Semiconductor Conference, 11-14 Oct. 2017, Sinaia, Romania, pp. 255-256, Accession Number: WOS:000425844500056, ISSN: 1545-827X, ISBN: 978-1-5090-3985-2, INSPEC Accession Number: 17353992, DOI: 10.1109/SMICND.2017.8101216, FI=0,25	ISI	6	0.250	5.417
19	A. Enache, I. Rusu, F. Draghici, G. Pristavu, G. Brezeanu, F. Enache, "High Accuracy Amperometric Sense and Control Circuit for Three-electrode Biosensors", ROMANIAN JOURNAL OF INFORMATION SCIENCE AND TECHNOLOGY, Volume: 19, Issue: 3, Pages: 295-308, Published: 2016, https://www.romjist.ro/content/pdf/enache.pdf, WOS:000405151400008, Q4 in Domeniul INSTRUMENTS & INSTRUMENTATION, IF=0,643 in anul depunerii, septembrie 2021	ISI	6	0.643	7.382
20	A. Enache, I. Rusu, F. Drăghici, Gh. Brezeanu, Gh. Pristavu, F. Enache, "Smart Sensor For Chemical Compounds Concentration", in Proc. of the 39th International Semiconductor Conference, 10-12 Oct. 2016, Sinaia, Romania, pp.201-204, DOI: 10.1109/SMICND.2016.7783086, Accession Number: WOS:000391323300041, ISBN: 9781509012077, ISSN: 1545827X, FI=0.25.	ISI	6	0.250	5.417
21	L. Teodorescu, F. Drăghici, I. Rusu, G. Brezeanu, "On Wafer High Temperature Characterization System", in Proc. of the 8th International Conference on Advanced Topics in Optoelectronics, Microelectronics, and Nanotechnologies (ATOMN), SEP 25-28, 2016, Constanta, Romania, pp. 8 , Accession Number: WOS:000391359600006, ISBN: 9781510604247; 9781510604254, ISSN: 0277786X, https://doi.org/10.1117/12.2247062, FI=0.25.	ISI	4	0.250	8.125
22	C. Ionescu, F. Drăghici, D. Bonfert, " A SPICE model for electroluminescent foils", in Proc. of the 38th International Spring Seminar on Electronics Technology (ISSE), 6-10 May 2015, Eger, Hungary, pp: 526 - 531, DOI: 10.1109/ISSE.2015.7248057, ISSN: 2161-2528, INSPEC Accession Number: 15439099, Accession Number: WOS:000374113000105, FI=0.25.	ISI	3	0.250	10.833
23	G. Brezeanu, M. Badila, F. Draghici, R. Pascu, G. Pristavu, F. Craciunoiu, I. Rusu, "High temperature sensors based on silicon carbide (SiC) devices", in Proc. of the 38th International Semiconductor Conference, 12-14 Oct. 2015, Sinaia, Romania, pp.3-10, DOI: 10.1109/SMICND.2015.7355147, ISBN: 978-1-4799-8862-4, ISSN: 1545-827X, INSPEC Accession Number: 15677965, Accession Number: WOS:000380566400001, FI=0.25.	ISI	7	0.250	4.643
24	G. Pristavu, A. Vasilica, V. Anghel, R. Pascu, G. Brezeanu, F. Draghici, "High voltage freewheeling diodes in an extended capability LED driving application", in Proc. of the 38th International Semiconductor Conference, 12-14 Oct. 2015, Sinaia, Romania, pp.175 - 178, DOI: 10.1109/SMICND.2015.7355199, ISBN: 978-1-4799-8862-4, ISSN: 1545-827X, INSPEC Accession Number: 15668027, Accession Number: WOS:000380566400033, FI=0.25.	ISI	6	0.250	5.417
25	N. Bădălan, P. Svasta, F. Drăghici, "Constant current versus pulse current for power supplies on high power LED", in Proc. of the 21st International Symposium for Design and Technology in Electronic Packaging (SIITME), 2015 IEEE, 22-25 Oct. 2015, Brasov, Romania, pp. 263 - 266, DOI: 10.1109/SIITME.2015.7342337, INSPEC Accession Number: 15648907, Accession Number: WOS:000377765500049, FI=0.25.	ISI	3	0.250	10.833
26	R. Pascu, G. Pristavu, M. Badila, G. Brezeanu, F. Draghici, F. Craciunoiu, "Temperature Behavior of 4H- SiC MOS Capacitor Used as a Gas Senzor", in Proc. of the 37th International Semiconductor Conference, 13-15 Oct. 2014, Sinaia, Romania, pp.185-188 (ISI), DOI: 10.1109/SMICND.2014.6966430, ISBN: 978-1-4799-3916-9, ISSN: 1545-827X, INSPEC Accession Number: 14788289, Accession Number: WOS:000380488300036, FI=0.25.	ISI	6	0.250	5.417
27	L. Teodorescu, A. Gheorghe, F. Draghici, G. Brezeanu, I. Rusu, "Power Supply Architecture for High Temperature Chuck Systems", in Proc. of the 37th International Semiconductor Conference, 13-15 Oct. 2014, Sinaia, Romania, pp.193-196 (ISI), DOI: 10.1109/SMICND.2014.6966432, ISBN: 978-1-4799-3916-9, ISSN: 1545-827X, INSPEC Accession Number: 14788282, WOS:000380488300038, FI=0.25.	ISI	5	0.250	6.500
28	G. Pristavu, F. Draghici, M. Badila, G. Brezeanu, R. Pascu, F. Craciunoiu, "High temperature SiC-sensors", In Proceedings of the 20th IEEE International Symposium for Design and Technology in Electronic Packaging (SIITME), OCT 23-26, 2014, Bucharest, ROMANIA, pp: 329-332, ISBN: 978-1-4799-6962-3, DOI: 10.1109/SIITME.2014.6967024, indexare ISI Web of Science, IDS: BD1QB, WOS:000358258300061, FI=0.25.	ISI	6	0.250	5.417
29	B. Ofrim, G. Brezeanu, F. Draghici, I. Rusu, "High Temperature Hydrogen Sensor Based on Silicon Carbide (SiC) MOS Capacitor Structure", Materials Science Forum 2014 cu titlul Silicon Carbide and Related Materials 2013, Vols. 778-780, 2014, pp. 1054-1057, ISSN: 0255-5476, DOI: 10.4028/www.scientific.net/MSF.778-780.1054, indexare ISI Web of Science, IDS: BA5GD, WOS:000336634100251, Q4 in Domeniul MATERIALS SCIENCE, MULTIDISCIPLINARY, IF=0.399 in anul publicarii	ISI	4	0.399	9.243

30	G. Brezeanu, F. Draghici, M. Badila, F. Craciunoiu, G. Pristavu, R. Pascu, F. Bernea, "Two Packaging Solutions for High Temperature SiC Diode Sensors", Materials Science Forum 2014 cu titlul Silicon Carbide and Related Materials 2013, 2014, pp. 1063-1066, ISSN: 0255-5476, https://doi.org/10.4028/www.scientific.net/MSF.778-780.1063 , indexare ISI Web of Science, IDS: BA5GD, WOS:000336634100253, Q4 în Domeniul MATERIALS SCIENCE, MULTIDISCIPLINARY, IF=0.399 in anul publicarii	ISI	7	0.399	5.281
31	F. Draghici, M. Pantazica, N. D. Codreanu, P. Svasta, "Hands-On Project - Key Issue in the Education of Future Electronic Engineers", In Proceedings of the 2014 37th International Spring Seminar on Electronics Technology (ISSE) - Advances in Electronic System Integration, Germany, May 07-11, 2014, pp: 468 - 473, ISSN: 2161-2528, ISBN: 978-1-4799-4455-2, DOI: 10.1109/ISSE.2014.6887646, indexare ISI Web of Science, IDS: BB8HC, WOS:000346580500093, FI=0.25.	ISI	4	0.250	8.125
32	G. Pristavu, G. Brezeanu, F. Draghici, "Two parameter extraction solutions for high temperature SiC Schottky diodes - Converging to reality", In Proceedings of the IEEE 19th International Symposium for Design and Technology in Electronic Packaging (SIITME), Oct. 24-27, 2013, pp: 181-184, ISBN:978-1-4799-1555-2, DOI: 10.1109/SIITME.2013.6743669, indexare ISI Web of Science, IDS: BB8UW, WOS:000347562900030, FI=0.25.	ISI	3	0.250	10.833
33	F. Draghici, M. Badila, G. Brezeanu, G. Pristavu, I. Rusu, F. Craciunoiu, R. Pascu, "4H-SiC Schottky Contact Improvement for Temperature Sensor Applications", in Proc. of the 36th International Semiconductor Conference (CAS), 14-16 oct. 2013, Sinaia, Romania, Vol. 2, pp. 163-166, ISBN:978-1-4673-5672-5; 978-1-4673-5670-1, ISSN: 1545-827X, DOI: 10.1109/SMICND.2013.6688645, WOS:000330180800033, FI=0.25.	ISI	7	0.250	4.643
34	A. B. Nae, G. Brezeanu, F. Draghici, "CMOS Current Reference With Improved Temperature Compensation", in Proc. of the 36th International Semiconductor Conference (CAS), Oct. 14-16 2013, Sinaia, Romania, Vol. 2, pp. 303-306, ISSN: 1545-827X, ISBN: 978-1-4673-5672-5; 978-1-4673-5670-1, indexare ISI Web of Science, IDS: BJT40, DOI: 10.1109/SMICND.2013.6688683, WOS:000330180800059, FI=0.25.	ISI	3	0.250	10.833
35	F. Draghici, G. Brezeanu, I. Rusu, F. Bernea, P. Godignon, "High Temperature SiC Sensor with an Isolated Package", Materials Science Forum 2013 cu titlul Silicon Carbide and Related Materials 2012, Vols. 740-742, 2013, pp. 1002-1005, ISSN: 0255-5476, ISBN: 978-3-03785-419-8, indexare ISI Web of Science, IDS: BFG56, DOI 10.4028/www.scientific.net/MSF.740-742.1002, WOS:000319785500239, Q4 în Domeniul MATERIALS SCIENCE, MULTIDISCIPLINARY, IF=0.399 in anul publicarii	ISI	5	0.399	7.394
36	L. Teodorescu, F. Draghici, G. Brezeanu, I. Rusu, "High Temperature Characterization System for Silicon Carbide Devices", in Proc. of the 35th International Semiconductor Conference (CAS), Oct. 15-17 2012, Sinaia, Romania, Vol. 2, IEEE Catalog Number: CFP12CAS-PRT, ISBN: 978-1-4673-0736-9, ISSN: 1545-827X, pp. 449-452, indexare ISI Web of Science, IDS: BDO53, DOI: 10.1109/SMICND.2012.6400734, WOS:000314223700093, FI=0.25.	ISI	4	0.250	8.125
37	R. Pascu, F. Craciunoiu, M. Kusko, F. Draghici, A. Dinescu, M. Danila, "The Effect of the Post-Metallization Annealing of Ni/n-type 4H-SiC Schottky Contact", in Proc. of the 35th International Semiconductor Conference, 15-17 Oct. 2012, Sinaia, Romania, vol. 2, IEEE Catalog Number: CFP12CAS-PRT, ISBN: 978-1-4673-0736-9, ISSN: 1545-827X, pp. 457-460, indexare ISI Web of Science, IDS: BDO53, DOI: 10.1109/SMICND.2012.6400732, WOS:000314223700095, FI=0.25.	ISI	6	0.250	5.417
38	G. Brezeanu, F. Draghici, M. Badila, I. Rusu, F. Bernea, P. Godignon, "A Fully Electrically Isolated Package for High Temperature SiC Sensors", Materials Science Forum 2012 cu titlul Silicon Carbide and Related Materials 2011, Vols. 717-720, 2012, pp. 925-928, ISSN: 0255-5476, ISBN: 978-3-03785-419-8, indexare ISI Web of Science, IDS: BCA44, DOI 10.4028/www.scientific.net/MSF.717-720.925, WOS:000309431000220, Q4 în Domeniul MATERIALS SCIENCE, MULTIDISCIPLINARY, IF=0.399 in anul publicarii	ISI	6	0.399	6.162
39	R. Pascu, F. Draghici, M. Badila, F. Craciunoiu, G. Brezeanu, A. Dinescu, I. Rusu, "High Temperature Sensor Based on SiC Schottky Diodes with Undoped Oxide Ramp Termination", in Proc. of the 34th International Semiconductor Conference, 17-19 Oct. 2011, Sinaia, Romania, Vol. 2, pp. 379-382, ISSN: 1545-827X, ISBN: 978-1-61284-171-7, DOI: 10.1109/SMICND.2011.6095823, indexare ISI Web of Science, IDS: BFK92, WOS:000320322000086, FI=0.25.	ISI	7	0.250	4.643
40	G. Brezeanu, F. Draghici, F. Craciunoiu, C. Boianceanu, F. Bernea, F. Udrea, D. Puscasu, I. Rusu, "4H-SiC Schottky Diodes for Temperature Sensing Applications in Harsh Environments", Materials Science Forum Vols. 679-680 (2011), pp. 575-578, https://doi.org/10.4028/www.scientific.net/MSF.679-680.575 , ISSN: 0255-5476, indexare ISI Web of Science, IDS: BVJ83, WOS:000291673500138, Q4 în Domeniul MATERIALS SCIENCE, MULTIDISCIPLINARY, IF=0.399 in anul publicarii	ISI	8	0.399	4.621
41	F. Draghici, M. Badila, G. Brezeanu, I. Rusu, F. Craciunoiu, I. Enache, "An Industrial Temperature Probe Based on SiC Diodes", in Proc. of the 33rd International Semiconductor Conference, 11-13 Oct. 2010, Sinaia, Romania, vol. 2, pp. 409-412, IEEE Catalog Number: CFP10CAS-PRT, ISBN: 978-1-4244-5971-6, ISSN: 1545-827X, DOI: 10.1109/SMICND.2010.5650596, Indexare, Google scholar, Scopus, IEEE - IEEEExplore- http://ieeexplore.ieee.org , indexare ISI Web of Science, IDS: BE3YT, WOS:000371396100084, FI=0.25.	ISI	6	0.250	5.417
42	F. Draghici, I. Rusu, G. Brezeanu, B. Bucur, "An Accurate Method For Measuring Very Low Frequency Biosignals", in Proc. of the 32nd International Semiconductor Conference, 12-14 Oct. 2009, Sinaia, Romania, pp. 423-426, ISSN: 1545-827X, ISBN: 978-1-4244-4413-7, DOI: 10.1109/SMICND.2009.5336688, indexare ISI Web of Science, IDS: BPO79, WOS:000279558600085, FI=0.25.	ISI	4	0.250	8.125
43	G. Brezeanu, A. Sevcenco, C. Boianceanu, I. Rusu, F. Draghici, "A Complete Analytical Submi-cron MOS Transistor Model for Analog Applications", in Proc. of the 31th International Semiconductor Conference, 13-15 Oct. 2008, Sinaia, Romania, pp. 309-312, ISBN: 978-1-4244-2004-9, DOI: 10.1109/SMICND.2008.4703411, indexare ISI Web of Science, IDS: BKA53, WOS:000267590800063, FI=0.25.	ISI	5	0.250	6.500
44	A. Sevcenco, G. Brezeanu, M.Badila, F. Draghici, I. Rusu, A Visoreanu, "Experimental Validation of a Simple Analytical Model for the Electrical Behavior of Nanoscale MOSFETs", in Proc. of the 30nd International Semiconductor Conference, 15-17 Oct. 2007, Sinaia, Romania, pp. 551-554, ISBN: 978-1-4244-0847-4, DOI: 10.1109/SMICND.2007.4519783, indexare ISI Web of Science, IDS: BHR98, WOS:000255865200120, FI=0.25.	ISI	6	0.250	5.417
45	G. Brezeanu, A. Visoreanu, M. Brezeanu, F. Udrea, G.A.J.Amaratunga I. Enache, I. Rusu, F. Draghici, "OFF- State performance of Ideal Schottky Barrier Diodes (SBD) on Diamond and Silicon Carbide", in Proc. of the 29nd International Semiconductor Conference, 27-29 Sept. 2006, Sinaia, Romania, pp. 319-322, ISBN: 1-4244-0109-7, DOI: 10.1109/SMICND.2006.284008, indexare ISI Web of Science, IDS: BFM58, WOS:000243090700066, FI=0.25.	ISI	8	0.250	4.063
46	G. Brezeanu, M. Badila, M. Brezeanu, F. Udrea, C. Boianceanu, I. Enache, F. Draghici, A. Visoreanu, "Breakdown performances improvements of SiC diodes using high-k dielectrics", in Proc. of the 28nd International Semiconductor Conference, 2-4 Oct., 2005, Sinaia, Romania, pp. 357-360, ISBN: 0-7803-9214-0, DOI: 10.1109/SMICND.2005.1558799, indexare ISI Web of Science, IDS: BEG01, WOS:000237180300078, FI=0.25	ISI	8	0.250	4.063
47	C. Boianceanu, G. Brezeanu, F. Udrea, G. Amaratunga, M. Brezeanu, A. Mihaila, F. Draghici, I. Enache, A. Visoreanu, "SiC Device Parameters Effects on the Electrical Behaviour of mCascode Switch" in Proc. of the 27nd International Semiconductor Conference, 4-6 Oct., 2004, Sinaia, Romania, pp. 389-392, ISBN: 0-7803-8499-7, DOI: 10.1109/SMICND.2004.1403026, indexare ISI Web of Science, IDS: BBV33, WOS:000228010700079, FI=0.25.	ISI	9	0.250	3.611
48	P. Agache, C. Boianceanu, F. Draghici, G. Dilimot, G. Brezeanu, "Data Acquisition and Processing for Semiconductor Devices", in Proc. of the 26th IEEE International Semiconductor Conference, September 28- October 2, 2003, Sinaia, Romania, pp. 223 - 226, ISBN: 0-7803-7821-0, indexare ISI Web of Science, IDS: BY80W, DOI:10.1109/SMICND.2003.1252422, WOS:000189468100047, FI=0.25.	ISI	5	0.250	6.500
49	G. Brezeanu, F. Udrea, A.Mihaila, G.Amaratunga, J. Millan, P. Godignon, M. Badila, F. Draghici, C. Boianceanu, M. Brezeanu, "Numerical and Analytical Study of 6H-SiC Detectors with High UV Performance", in Proc. of the 25th IEEE International Semiconductor Conference, 2002, Sinaia, Romania, pp. 185-188, ISBN: 0-7803-7440-1, indexare ISI Web of Science, IDS: BW34A, DOI: 10.1109/SMICND.2002.1105827, WOS:000181629400039, FI=0.25.	ISI	10	0.250	3.250
50	F. Draghici, F. Mitu, G. Brezeanu, M. Badila, C. Boianceanu, P. Agache, I. Enache, "Electrical and Optical Behavior of the SiC Photodetectors", in Proc. of the 25nd IEEE International Semiconductor Conference, 8-12 Oct., 2002, Sinaia, Romania, pp.195 -198, ISBN: 0-7803-7440-1, indexare ISI Web of Science, IDS: BW34A, DOI: 10.1109/SMICND.2002.1105829, WOS:000181629400041, FI=0.25.	ISI	7	0.250	4.643

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52	M. Badila, G. Brezeanu, V. Banu, P. Godignon, J. Millan, X. Jorda, F. Drăghici, "SiC power Schottky diodes industrial development", in Proc. of the 24th IEEE International Semiconductor Conference, 9-13 Oct., 2001, Sinaia, Romania, pp. 337 - 340, ISBN: 0-7803-6666-2, indexare ISI Web of Science, IDS: BU24V, DOI: 10.1109/SMICND.2001.967478, WOS:000175459600070, FI=0.25.	ISI	7	0.250	4.643
53	F. Mitu, F. Drăghici, G. Dilimot, C. Amiroaie, I. Vladan, "A Characterisation Technique for High Power/Temperature Devices Using HP4275/3437 Systems", in Proc. of the 23rd IEEE International Semiconductor Conference, 10-14 Oct. 2000, Sinaia, Romania, pp. 337-340, ISBN: 0-7803-5885-6, indexare ISI Web of Science, IDS: BPO79, DOI: 10.1109/SMICND.2000.890251, WOS:000168560900068, FI=0.25.	ISI	5	0.250	6.500
54	F. Drăghici, F. Mitu, G. Dilimot, I. Enache, "Method to increase the thermal stability of the heating circuits", in Proc. of the 21th International Semiconductor Conference, 6-10 Oct. 1998, Sinaia, Romania, pp. 501-504, ISBN: 0-7803-4432-4, indexare ISI Web of Science, IDS: BM44W, DOI: 10.1109/SMICND.1998.733795, WOS:000078772400094, FI=0.25.	ISI	4	0.250	8.125
55	F. Mitu, F. Drăghici, G. Dilimot, G. Brezeanu, I. Enache, "GTO gating circuit by open cathode method", in Proc. of the 20th International Semiconductor Conference, 7-11 Oct. 1997, Sinaia, Romania, pp. 123-126, ISBN: 0-7803-3804-9, indexare ISI Web of Science, IDS: BK43M, DOI: 10.1109/SMICND.1997.651562, WOS:000072168800020, FI=0.25.	ISI	5	0.250	6.500
A2.2 Articole în reviste, și în volumele unor manifestari stiintifice indexate în alte baze de date internationale recunoscute (BDI) [4]		Baza de date [4]	Nr. Autori		
1	G. Pristavu, G. Brezeanu, M. Badila, F. Drăghici, R. Pascu, F. Craciunoiu, I. Rusu, A. Pribeanu, "High Temperature Behavior Prediction Techniques for Non-Uniform Ni/SiC Schottky Diodes", Materials Science Forum, Vol. 924, pp. 967-970, 2018, Trans Tech Publication, DOI: 10.4028/www.scientific.net/MSF.924.967	Scopus	8		2.500
2	G. Pristavu, G. Brezeanu, M. Badila, F. Drăghici, R. Pascu, F. Craciunoiu, I. Rusu, A. Pribeanu, "Barrier Stability of Pt/4H-SiC Schottky Diodes Used for High Temperature Sensing", Materials Science Forum, Vol. 897, cu titlul - Silicon Carbide and Related Materials 2016, pp. 606-609, May 2017, ISSN: 02555476, ISBN: 978-303571043-4, DOI: 10.4028/www.scientific.net/MSF.897.606	Scopus	8		2.500
3	G. Pristavu, G. Brezeanu, M. Badila, F. Drăghici, R. Pascu, F. Craciunoiu, "An Investigation of SiC Schottky Contact Barrier Inhomogeneity for Temperature Sensing Applications", Materials Science Forum, Vol. 858, pp. 577-581, 2016, https://doi.org/10.4028/www.scientific.net/MSF.858.577	Scopus	6		3.333
4	R. Pascu, G. Pristavu, G. Brezeanu, F. Drăghici, M. Badila, I. Rusu, F. Craciunoiu, "Electrical Characterization of Ni-Silicide Schottky Contacts on SiC for High Performance Temperature Sensor", Materials Science Forum, Vols. 821-823, pp. 436-439, 2015, DOI 10.4028/www.scientific.net/MSF.821-823.436	Scopus	7		2.857
5	L. Teodorescu, A. S. Gheorghe, F. Drăghici, "Digital signage equipment for gas station pumps application", U.P.B. Sci. Bull., Series C, Vol. 75, Iss. 4, 2013, ISSN 2286 – 3540, pp. 57-68, indexare B+, la https://www.scientificbulletin.upb.ro/rev_docs_arhiva/full255_124795.pdf, Scopus	Scopus	3		6.667
6	G. Brezeanu, F. Drăghici, C. Boianeanu, "SiC photodetectors with high UV selectivity and sensitivity", Romanian Journal of Physics, vol. 48, nr.1-4, 2003, pp.171-184, ISSN 1221-146X, indexat in Science Citation Expanded (SciSearch®) and Journal Citation Reports/Science Edition, JCR 2012, https://rjp.nipne.ro/2003_48_1-4.html, FI (2012)=0.526	Science Direct	3		6.667
7	M. Badila, G. Brezeanu, J. P. Chante, Marie-Laure Locatelli, J. Millan, P. Godignon, P. Lungu, F. Mitu, F. Drăghici, F. J. Campos, A. Lebedev, V. Banu, G. Banoiu, "A Technique To Avoid Micropipe Effects on 6H-SiC Power Devices", in Proc. of the 22nd International Semiconductor Conference, 5-9 Oct., 1999, Sinaia, Romania, pp. 187 - 190, IEEE Catalog Number: 99TH8389, ISBN: 0-7803-513 9-8 Softbound Edition, 0-7803-5140-1 Microfiche Edition, IEEE - IEEEXplore, http://ieeexplore.ieee.org. DOI: 10.1109/SMICND.1999.810459	IEEE Explore	13		1.538
A2.3.1 Proprietate intelectuală, brevete de invenție, certificate ORDA - internationale [5]		Înregistrat la [5]:	Nr. Autori	Factor impact [12]	
				0.000	0.000
A2.3.2 Proprietate intelectuală, brevete de invenție, certificate ORDA - nationale (OSIM)		Înregistrat la [5]:	Nr. Autori	Factor impact [12]	
1	F. Drăghici, F. Mitu, "Interfața analogică", Brevet de invenție, Nr. 122980, 28.05.2010, Oficiul de stat pentru invenții și mărci (OSIM), Romania, prezent în baza ISI ca Patent Number: RO122980-B1, Accession Number: DIIDW:2010K27053, https://ro.espacenet.com/publicationDetails/biblio?FT=D&date=20100528&DB=ro.espacenet.com&locale=ro_RO&CC=RO&NR=122980B1&KC=B1&ND=5		2	0.500	12.500
A2.4.1.1 Granturi / proiecte de cercetare câștigate prin competiție [6] sau Contracte cu agenți economici în valoare de minim 10.000 dolari SUA echivalent încasați [6] (Director / responsabil partener) - internaționale		[6]	Nr.ani		
					0.000
A2.4.1.2 Granturi / proiecte de cercetare câștigate prin competiție [6] sau Contracte cu agenți economici în valoare de minim 10.000 dolari SUA echivalent încasați [6] (Director / responsabil partener) - naționale			Nr.ani		
1	"Senzori și sisteme integrate electronice și fotonice pentru securitatea persoanelor și a infrastructurilor (SENSIS)", PN-III-P1-1.2-PCCDI2017-0419, proiectul component P2: "Senzori de hidrocarburi pe SiC pentru securitatea în exploatare în medii industriale ostile (SiC-SENS)". Derulare: 2017-2021, Responsabil din partea UPB pe proiectul component P2: Florin Drăghici, https://sensis-ict.ro/senzori-de-hidrocarburi-pe-sic-pentru-masurarea-concentrațiilor-de-hidrogen-si-hidrocarburi/		3.25		32.500
2	"Rezonatori de tip SAW și FBAR dedicați aplicațiilor în comunicații pentru gama 2-6 GHz și în domeniul senzorilor, obținuți prin tehnici de microprelucrare și nanoprocesare a semiconducătorilor de banda largă GaN și AlN, GIGASABAR", Proiecte Complexe PNII, PARTENERIATE ÎN DOMENIILE PRIORITARE, Derulare: 2007-2010, Responsabil din partea UPB: Florin Drăghici, https://www.imt.ro/gigasabar/consortium.php		3.00		30.000
A2.4.2.1 Granturi / proiecte de cercetare câștigate prin competiție [6] sau Contracte cu agenți economici în valoare de minim 10.000 dolari SUA echivalent încasați [6] în calitate de Membru în echipă - internaționale			Nr.ani		
1	Bilateral cooperation - Periphery isolation for 4H-SiC high frequency power p-i-n diodes with applications in wireless communications, with Foundation for Research & Technology-Hellas (FORTH), Heraklion, Crete, Greece 2003-2005. Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici.		2.00		8.000
2	Microserv Project, "High Temperature SiC Power Schottky Diode", Politechnic University of Bucharest, Romania", 2000-2002, Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici.		2.00		8.000
3	Contract D107 cu Banca Mondială, "Dispozitive, circuite și microsisteme electronice", derulare 1999-2000, Director contract UPB: Prof. Adrian Rusu, participant: F. Drăghici.		2.00		8.000

4	INCO-Copernicus – Proiect: 960211/1996, "Lely SiC High Temperature Power Diode Fabrication (PODILESCA)", 1996 – 1998, (finanțat de U.E.). Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici .		2.00		8.000
	A2.4.2.2 Granturi / proiecte de cercetare câștigate prin competiție [6] sau Contracte cu agenți economici în valoare de minim 10.000 dolari SUA echivalent încasați [6] în calitate de Membru în echipă - naționale		Nr.ani		
1	275-PED/2020, "Senzori PTAT de înaltă temperatură cu diode Schottky pe SiC pentru monitorizare și securitate în medii industriale ostile (SiC-HITS)", Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici , derulare 2020-2022, 2 ani.		2.00		4.000
2	PN-III-P2-2.1-PED-2019-4146/ PED 333/2020, "Dispozitiv electrochimic modular pentru stocarea de sarcină", acronim MSTODE, Responsabil de proiect UPB: Eugeniu Vasile, membru în echipa de cercetare: F. Drăghici , derulare 2020-2022, 2 ani.		2.00		4.000
3	Proiect cofinanțat din Fondul Social European (FSE), prin Programul Operațional Capital Uman (POCU) 2014-2020, Axa Prioritară 6- Educație și competențe, Cod SMIS 125125, Nr.contract: 51675/09.07.2019, "Dezvoltarea competențelor de antreprenoriat ale doctoranzilor și postdoctoranzilor – cheia a succesului în carieră (A-Succes)", Manager proiect: Prof. Horia IOVU, membru în echipa de implementare - Expert calitate programe doctorale 3, Florin Draghici , 10.07.2019 - 09.01.2021.		1.50		3.000
4	Proiect co-finanțat din Fondul European de Dezvoltare Regională prin Programul Operațional Competitivitate 2014-2020, Cod MySmis: 105976, "NETIO - Ecosistem de cercetare, inovare și dezvoltare de produse și servicii TIC pentru o societate conectată la Internet of Things", Director de proiect - Prof. Adina Magda FLOREA, Responsabil tehnic teme de cercetare, F. Drăghici		1.00		2.000
5	Proiect PN-III-P2-2.1-PED-2016-0503 contract Nr.180 PED/2017 „Metodă rapidă de analiză bazată pe biosenzor enzimatic pentru determinarea aspartamului din alimente ” (ASPSSENS). UPB în parteneriat cu INCDSB (INSB)-coordonator, Responsabil proiect UPB, Conf.dr.ing. RUSU Ion, în derulare 2017-2019. Membru în echipa de cercetare, F. Drăghici .		1.50		3.000
6	PN-II-PT-PCCA-2011,nr.146/2014, "Sistem multiparametric pentru monitorizarea fermentării vinului", Responsabil proiect UPB, Conf.dr.ing. RUSU Ion, Derulare: 2014-2017. Membru în echipa de cercetare, F. Drăghici .		2.83		5.660
7	Proiect PN-II-PCCA, 21/2-0479/PN-II-PT-PCCA-2011-3.2-0487, "Senzor inteligent de temperaturi ridicate cu diode pe carbură de siliciu (SiC) pentru aplicații industriale în medii ostile, SiC-SET", Director de proiect UPB: Gheorghe Brezeanu, membru în echipa de cercetare (persoană cheie): F. Drăghici , derulare 2012-2016, 4,5 ani.		4.50		9.000
8	Proiect PN-II-PCCA Nr. 204/2012, "Detector de gaze inflamabile și toxice bazat pe matrice de senzori MOS pe carbură de siliciu, SiC-GAS", Responsabil de proiect UPB: Gheorghe Brezeanu, membru în echipa de cercetare (persoană cheie): F. Drăghici , derulare 2012-2016, 4,5 ani.		4.50		9.000
9	Parteneriat PN2, DIASENZOR – D-11062, "Diode senzor pe Diamant și SiC pentru aplicații speciale în industria cimentului", Director de proiect UPB: Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici , derulare 2007-2010, (5 faze), 3 ani.		3.00		6.000
10	Grant/ platforma CNCISIS - "Platforma ingineria integrată a autovehiculelor – AUTOINTEGRING", coordonator proiect UPB- Catedra de autovehicule rutiere, 2006-2008, Director de proiect: Prof. C. Andreescu, Membru în echipa de cercetare, F. Drăghici .		2.00		4.000
11	Grant CNCISIS, "Fotodiode de mare eficiență pe carbură de siliciu pentru detecția radiațiilor ultraviolete", 2004-2006, (3 faze). Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici		2.00		4.000
12	Contract RELANSIN - 375/24/12/1999, "Dispozitive Schottky pe carbură de siliciu pentru aplicații speciale de putere și temperatură", Beneficiar: Agenția Managerială de Cercetare Științifică, Inovare și Transfer Tehnologic – Politehnica din București, 1999 – 2002, cinci faze, Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici		3.00		6.000
13	Grant ANSTI – 5076 – A63 (15.02.07), "Caracterizarea și testarea dispozitivelor pe SiC pentru aplicații speciale de putere și temperatură" (continuarea lui A25), 2002. Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici		1.00		2.000
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15	Grant ANSTI – 5076 – B77 (15.99.16), "Caracterizarea și testarea dispozitivelor pe SiC", 1999. Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici		1.00		2.000
16	Grant ANSTI – 3042 – A16 (15.97.14), "Fizica interfeței SiO2 – SiC cu aplicații la tranzistoare MOS și diode Schottky", 1997. Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici		1.00		2.000
17	Grant MEN – B961 (15.97.11), "Modelarea procesului de comutație a dispozitivelor semiconductoare",1997. Director de proiect UPB: Prof. Gheorghe Brezeanu, membru în echipa de cercetare: F. Drăghici		1.00		2.000
Total A2			36.517		664.037

Nr.crt.

A3 - Recunoașterea și impactul activității					
A3.1.1 Citări [7] în cărți, reviste și volume ale unor manifestări științifice - cărți, ISI [8]					
	Baza de date	Nr. Autori articol citat	[7], [8]	Punctaj	
	Articol citat: R. Pascu , G. Pristavu, G. Brezeanu, F. Draghici , P. Godignon, C. Romanitan, M. Serbanescu, A. Tulbure, "60–700 K CTAT and PTAT Temperature Sensors with 4H-SiC Schottky Diodes", Sensors 2021, 21(3), 942; pp. 1–15, publicare online, https://doi.org/10.3390/s21030942 , eISSN: 1424-8220, WOS:000615521900001				
1	ISI-Q1	8			2.000
	D. Lero, M. Merenda, R. Carotenuto, G. Pangallo, S. Rao, G. Brezeanu, F. G. Della Corte, "A Technique for Improving the Precision of the Direct Measurement of Junction Temperature in Power Light-Emitting Diodes", Sensors 2021, 21(9), 3113; https://doi.org/10.3390/s21093113 , WOS:000650769200001				
2	ISI-Q2	8			2.000
	R. Pascu, C. Romanitan, "Phase transition of nickel silicide compounds and their electrical properties", J Mater Sci: Mater Electron (2021). https://doi.org/10.1007/s10854-021-06238-1 ISSN: 0957-4522, eISSN: 1573-482X, WOS:000655890600002				
	Articol citat: F. Draghici , G. Brezeanu, G. Pristavu, R. Pascu, M. Badila, A. Pribeanu, E. Ceuca, "400°C Sensor Based on Ni/4H-SiC Schottky Diode for Reliable Temperature Monitoring in Industrial Environments". Sensors 2019, 19, 2384, WOS:000471014500171				
1	ISI	7			1.143
	R. Pascu, C. Romanitan, "Phase transition of nickel silicide compounds and their electrical properties", J Mater Sci: Mater Electron (2021). https://doi.org/10.1007/s10854-021-06238-1 , Pages: 16811-16823, ISSN: 0957-4522, eISSN: 1573-482X, WOS:000655890600002				

2	K. Zeghdar, L. Dehimi, F. Pezzimenti, ML. Megherbi, FG. Della Corte, "Analysis of the Electrical Characteristics of Mo/4H-SiC Schottky Barrier Diodes for Temperature-Sensing Applications", JOURNAL OF ELECTRONIC MATERIALS, Vol. 49, Issue: 2, Pp. 1322-1329, DOI: 10.1007/s11664-019-07802-6, Published: FEB 2020, ISSN: 0361-5235, eISSN: 1543-186X, WOS:000511718200050	ISI	7		1.143
3	S.J. Min, MC. Shin, NT. Nguyen, JM. Oh, SM. Koo, "High-Performance Temperature Sensors Based on Dual 4H-SiC JBS and SBD Devices", MATERIALS, Vol. 13, Issue: 2, Article Number: 445, DOI: 10.3390/ma13020445, JAN 2 2020, PubMed ID: 31963426, eISSN: 1996-1944, WOS:000515499900192	ISI-Q2	7		2.286
4	O. Çiçek, Ş. Altındal and Y. Azizian-Kalandaragh, "A Highly Sensitive Temperature Sensor Based on Au/Graphene-PVP/n-Si Type Schottky Diodes and the Possible Conduction Mechanisms in the Wide Range Temperatures," in IEEE Sensors Journal, vol. 20, no. 23, pp. 14081-14089, 1 Dec.1, 2020, doi: 10.1109/JSEN.2020.3009108., WOS:000589257300025	ISI-Q2	7		2.286
5	A.M. Nawar, A.M. El-Mahalawy, "Heterostructure device based on Brilliant Green nanoparticles-PVA/p-Si interface for analog-digital converting dual-functional sensor applications", J Mater Sci: Mater Electron 31, 3256–3273 (2020). https://doi.org/10.1007/s10854-020-02874-1 , WOS:000514597300054	ISI-Q2	7		2.286
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1	D. Iero, M. Merenda, R. Carotenuto, G. Pangallo, S.D. Rao, G. Brezeanu, FG.Della Corte, "A Technique for Improving the Precision of the Direct Measurement of Junction Temperature in Power Light-Emitting Diodes", SENSORS, Volume: 21 Issue: 9, Article Number: 3113, DOI: 10.3390/s21093113, MAY 2021, eISSN: 1424-8220, WOS:000650769200001	ISI-Q1	5		3.200
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4	LA Li, XB. Li, TF. Pu, SH. Cheng, HD. Li, JP. Ao, "Vertical GaN-Based Temperature Sensor by Using TiN Anode Schottky Barrier Diode", IEEE SENSORS JOURNAL, Volume: 21 Issue: 2, Pp: 1273-1278, JAN 15, 2021, DOI: 10.1109/JSEN.2020.3018330, ISSN: 1530-437X, eISSN: 1558-1748, WOS:000609903000040	ISI-Q2	5		3.200
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1	Pol Ribes-Pleguezuelo, Nicolaie Pavel, Erik Beckert, Christoph Damm, Axel Bodemann, Oana-Valeria Grigore, Gabriela Croitoru, Catalina-Alice Brandus, Nicolae-Tiberius Vasile, Ramona Eberhardt, Andreas Tünnermann, "Assembly process and optical performances for a golden laser spark-plug device," Opt. Eng. 58(6) 065101 (13 June 2019), https://doi.org/10.1117/1.OE.58.6.065101 , ISSN: 0091-3286, eISSN: 1560-2303, WOS:000481889800019	ISI	7		1.143
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1	Vit Malinovsky, "System Macromodel of Agricultural Building with Aim to Energy Consumption Minimization", <i>Agris On-Line Papers in Economics & Informatics</i> . Mar2018, Vol. 10 Issue 1, p25-35. 11p, https://scholar.google.ro/scholar?oi=bibs&hl=ro&ites=14433228815614064465	Scopus	7		0.571
	Articol citat: F. Drăghici , X. Jorda, G. Brezeanu, M. Badila, J. Millan, P. Godignon, "A System for Measure Reverse Recovery Time and Stored Charge at Ultrafast Power Diodes", in <i>Proc. of the 24th IEEE International Semiconductor Conference</i> , 9-13 Oct., 2001, Sinaia, Romania, pp. 473 – 476, ISBN: 0-7803-6666-2, indexare ISI Web of Science, IDS: BU24V, WOS:000175459600100, FI=0.25.				
1	C.-Y.Ahn, J.-S. Kim, "Analysis of ZCS operation characteristics of GaN FET-based IPT system", (2020) 69 (9), pp. 1356-1363, https://www.scopus.com/inward/record.uri?eid=s2-0-85091464424&doi=10.5370%2fKIEE.2020.69.9.1356&partnerID=40&md5=ad21461a71ab6c750045bb58ee162294 , DOI: 10.5370/KIEE.2020.69.9.1356	Scopus	6		0.667
	A3.2 Membru în colective de redacție sau comitete științifice ale revistelor indexate ISI, chair, co-chair sau membru în comitetele de organizare ale manifestărilor științifice internaționale indexate ISI [9]	Baza de date	[9]		
1	Membru al Paper Review Board International Semiconductor Conference - CAS, Sinaia, Romania, din 2011	ISI			10.000
2	Membru in International Steering Committee, SIITME, Oradea 2016	ISI			10.000
3	Chairman la International Semiconductor Conference - CAS, Sinaia, Romania, din 2013	ISI			10.000

4	Recenzie ECSCRM 2012	ISI			10.000
5	Associate Editor, ROMJIST, din 2017	ISI			10.000
6	Recenzor SENSORS, 2019	ISI-Q1			10.000
7	Recenzor JAP 2019	ISI-Q2			10.000
	A3.3 Membru în colective de redacție sau comitete științifice ale revistelor indexate BDI, chair, co-chair sau membru în comitetele de organizare ale manifestărilor științifice internaționale indexate BDI [9]	Baza de date			
1	Recenzii la Revista Buletin Științific al Universității Politehnica din Bucuresti, din 2019	Scopus			6.000
	A3.4 Premii în domeniu conferite de Academia Română, ASTR, AOSR, sau premii internaționale de prestigiu				
	Total A3				300.290

Conf. dr. ing. Florin DRĂGHICI